

AMENDMENTS TO THE CLAIMS

1-16. (cancelled)

17. (original) A method of forming a patterned material structure on a substrate, said material being selected from the group consisting of semiconductors, ceramics and metals, said method comprising:

- (A) providing a substrate with a layer of said material,
- (B) applying a resist composition to said substrate to form a resist layer on said substrate, said resist composition comprising (a) an imaging polymer, and (b) a radiation sensitive acid generator, said imaging polymer comprising cyano-modified acrylic monomer units comprising an acrylic moiety with a cyano group pendant therefrom;
- (C) patternwise exposing said substrate to radiation whereby acid is generated by said acid generator in exposed regions of said resist layer by said radiation,
- (D) contacting said substrate with an aqueous alkaline developer solution, whereby said exposed regions of said resist layer are selectively dissolved by said developer solution to reveal a patterned resist structure, and
- (E) transferring resist structure pattern to said material layer, by etching into said material layer through spaces in said resist structure pattern.

18. (original) The method of claim 17 wherein said material is metal.
19. (original) The method of claim 17 wherein said etching comprises reactive ion etching.
20. (original) The method of claim 17 wherein at least one intermediate layer is provided between said material layer and said resist layer, and step (E) comprises etching through said intermediate layer.
21. (original) The method of claim 17 wherein said radiation has a wavelength of about 193 nm.
22. (original) The method of claim 17 wherein said substrate is baked between steps (C) and (D).
23. (original) The method of claim 17 wherein said imaging polymer contains cyclic olefin monomeric units in a backbone portion of said polymer, and/or (ii) alicyclic moieties as bulky end groups.